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(54) Title: EQUIPMENT AND PROCESS TECHNOLOGIES FOR CATALYST INFLUENCED CHEMICAL ETCHING

(57) Abstract: A method and system for etching a semiconductor substrate using catalyst influenced chemical etching. A group of independently controlled discrete actuators are configured to control a depth of an etch of a material on a substrate, where at least two of the group of independently controlled discrete actuators has distinct actuation values. Furthermore, the etch depth has a variation of less than 10% of a feature height across the substrate.



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